5 é / Descriptions

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Ultrafast Recovery Diode in a TO-220AC Plastic Package.

¤ ª / Features

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Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

Ð ÷ / Applications

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For high frequency, high voltage, high current rectifier diode, freewheeling diode.

Ã W] Ô · / Equivalent Circuit

• Û - æ / Pinning

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PIN1o•2 y Cathode PIN 3 y Anode

Z Ü B , M V / h_{FE} Classifications & Marking

• - ~ ª ¢ož See Marking Instructions

Ã a ? d / Absolute Maximum Ratings(Ta=25 ;)

@ ƒ Parameter	… Z Symbol	ƒ › Rating	% y Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Average Forward Current	I_F	1 h 10	A
Peak forward surge current	I_{FSM}	100	A
Typical Thermal Resistance Junction to Case	R_{Jc}	1.5	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

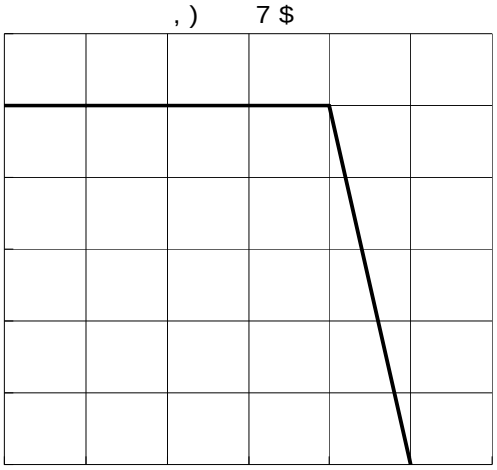
Ô4ì × ? d / Electrical Characteristics(Ta=25 ;)

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Reverse Voltage	V_R	I_R=1mA	600			V
Forward Voltage	V_F	I_F=2.0A T_C=25		1.0	1.2	V
		I_F=2.0A T_C=150		0.73	1.0	
		I_F=10A T_C=25		1.3	1.5	
		I_F=10A T_C=150		1.1	1.2	
Instantaneous Reverse Current(Note1)	I_R	V_R=600V T_a=25			10	A
		V_R=480V T_a=150			100	
		V_R=600V T_a=150			500	
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A			50	ns

h Notes Ö

1. … â ? y ¡ ž • k Y @ O × 5 ½ | •ož Short duration pulse test used to minimize self-heating effect.
2. ” ³ Ô ð h ¢ k ƒ › %² / Ì @ ƒož Unless otherwise noted, values for the parameters of a single chip

Ô ? d • Ž ¢ / Electrical Characteristic Curve



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, M y ƒ / Marking Instructions

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Note:

BR:	Company Code
MUR1060 y	Product Type.
****:	Lot No. Code, code change with Lot No.